Surface phonons limit heat conduction in ultra-thin films

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Abstract \\
We applied anharmonic lattice dynamics methods to microscopically investigate phonon transport in ultra-thin films and evaluated the applicability and validity of the Sondheimer theory, which is widely used for analyzing heat conduction in thin films. We found that the presence of a surface yields surface-localized phonons (surface phonons); moreover, anharmonic phonon coupling between surface and inner phonons localized within the thin film significantly suppresses overall heat conduction in the thin film, which cannot be explained by the Sondheimer theory. This study clarifies the role of surface phonons in heat conduction and provides useful information for electronic and phononic devices.
Understanding the microscopic phonon transport properties of thin films is essential for the thermal management of microelectronics[1] and phononic crystals[2]. The Sondheimer theory[3] has been widely used for evaluating the heat conduction of thin films and has been shown to reproduce the thermal conductivities of thin films thicker than 50 nm. This model incorporates phonon scattering at the surface of thin films in terms of specularity in the phonon Boltzmann transport equation. In general, bulk phonon transport properties are used for this theory. However, the applicability of this theory is debatable when the thickness approaches several nanometers because the presence of a surface modulates phonon dispersion relations, leading to changes in the group velocity and scattering phase space[4,5].

In addition to these modulations, the presence of a surface also yields surface-localized phonon modes, namely, surface phonons. In ultra-thin films with a thickness of less than 10 nm, the specific surface area is large; thus, surface phonons should play an essential role in heat conduction. However, few works have studied the impact of surface phonons on the overall heat conduction in ultra-thin films. Here, we applied an anharmonic lattice dynamics (ALD) method[6] to silicon ultra-thin films by explicitly considering the atomic structure of the thin films. In addition, we investigated the applicability and validity of the Sondheimer theory as well as the role of surface phonons in heat conduction within thin films.

We considered thin films with \(\langle 100\rangle\), \(\langle 110\rangle\), and \(\langle 111\rangle\) surface orientations. A unit cell for each surface orientation is illustrated in Fig. 1(a). The lattice constants of the three surface orientations are 0.546 nm \((\langle 100\rangle)\), 0.386 nm \((\langle 110\rangle)\), and 0.945 nm \((\langle 111\rangle)\).
A thin film with a given thickness was modeled by stacking unit cells along the z-direction perpendicular to the surface, sandwiched by vacuum layers at the top and bottom surfaces. Although surface reconstruction and changes in the bond lengths of surface atoms generally occur, these phenomena are not considered to enable comparison with a bulk-adopted method[7] and to evaluate the influence of surface phonons on the overall heat conduction in a thin film. To enhance the influence of surface phonons on transport properties, the outermost surface atoms of the \( \langle 111 \rangle \) surface orientation, which is usually unstable, were retained.

First-principles calculations can be performed to obtain the interatomic force constants (IFCs) needed to calculate transport properties[8,9]. However, because the approximately 10-nm-thick film considered in this work includes several hundreds of atoms, the use of first-principles calculations is not practical. Therefore, we employed the empirical Stillinger–Weber potential[10,11], whose parameters are optimized to reproduce the phonon dispersion relation and thermal conductivity of bulk silicon. Harmonic and third-order anharmonic IFCs were considered, and these interaction ranges were set to second and first nearest neighbors, respectively. In the ALD calculations, we chose a \( 20 \times 20 \) uniform reciprocal mesh in a two-dimensional Brillouin zone for calculating transport properties and a \( 7 \times 7 \) uniform mesh only for an 11-nm-thick film with \( \langle 100 \rangle \) surface orientation. The Dirac delta function associated with energy conservation in three-phonon scattering was approximated by a Lorentzian function. The linewidth of the Lorentzian was appropriately chosen to ensure convergence. We used the LAMMPS[12] and ALAMODE[6] packages for all
The calculated phonon dispersion relations for thin films with the \{100\} surface orientation are shown in Figs. 1(b,c) for two thicknesses. The thinnest film has an out-of-plane acoustic phonon mode whose angular frequency (\(\omega\)) is proportional to the square of the wavevector (\(k\)) near the zone center. This feature has been observed in two-dimensional materials such as graphene. As the thickness increases, the \(\omega \propto k^2\) dependence changes to \(\omega \propto k\), exhibiting a form of three-dimensional vibrational modes inside the film. Another remarkable feature is the presence of isolated phonon modes. While the magnitude of the modulation of the phonon dispersion relation varies with the thickness, isolated phonon modes can be readily found, even for relatively thick films, corresponding to surface-localized modes, i.e., surface phonons. For the 5.5-nm thin film [Fig. 1(c)], one can see five surface phonon modes, labeled S\(_1\)–S\(_5\). From eigenvector analysis, surface phonon modes S\(_1\) and S\(_2\) are identified as the Love wave (horizontal shear wave) and Rayleigh wave (vertical shear wave), respectively. Surface phonons can also be detected by the bulk-adopted method[7], in which perturbations of harmonic IFCs are eliminated among surface atoms by applying a periodic boundary condition in the direction perpendicular to the surface. A simple comparison between dispersion relations enables us to easily find isolated phonon modes in the low-frequency regime (Figs. S1–S3)[13].

For the \{100\} surface orientation, the dispersions of the surface phonons are dispersive. In contrast, those for the \{111\} surface-orientation are nearly flat (Fig. S3). In contrast, for the \{110\} surface orientation, surface phonons cannot be identified from the
dispersion relations based on comparison to the bulk-adopted method (Fig. S2). The characteristics of the surface phonons are strongly dependent on the surface orientation, which is attributed to the coordination number of the outermost surface atoms. For the \(\langle 110\rangle\), \(\langle 100\rangle\), and \(\langle 111\rangle\) orientations, the coordination numbers are three, two, and one, respectively. Thus, the harmonic IFC perturbations are the smallest for surface atoms with the \(\langle 110\rangle\) surface orientation, and the extent of isolation for the surface phonons is quite low.

We display the calculated thermal conductivities \(\kappa\) for the three surface orientations at \(T = 300\) K in Fig. 2(a). Because the heat conduction for the \(\langle 110\rangle\) case is anisotropic, \(\kappa\) is averaged in the \(x\)- and \(y\)-directions. In all cases, \(\kappa\) monotonically increases with increasing thickness; however, the thickness dependence of \(\kappa\) varies according to the surface orientation. Because dispersion relations that explicitly account for the atomic structure of a thin film differ from bulk dispersion relations, the validity of bulk phonon transport properties as inputs for the Sondheimer theory is questionable. Nevertheless, the \(\kappa\) results are similar to the curves obtained by the Sondheimer theory. By comparing the spectral \(\kappa\) results with those calculated by the Sondheimer theory with a surface specularity of \(p = 0.8\) [Figs. 2(b,c)], the spectral \(\kappa\) of the 0.55-nm thin film is found to be different from that obtained by the Sondheimer theory with \(p = 0.8\) throughout the entire frequency regime. In particular, a large discrepancy between the spectral \(\kappa\) results for the 5.5-nm thin film and the Sondheimer theory calculations with \(p = 0.8\) arises in the low-frequency regime. In contrast, the two spectral \(\kappa\) curves are fairly well matched at frequencies above approximately 7 THz. Thus, by tuning \(p\), the
Sondheimer theory may be able to reproduce the calculated thickness-dependent $\kappa$.

In line with Ziman’s formula[14], $p$ can be expressed by the phonon wavelength $\lambda$ and surface roughness $\eta$; $p(\lambda) = \exp(-16\pi^3\eta^2/\lambda^2)$. Although the thin films considered in this work do not have surface roughness, we can extract $\eta$ by fitting the Sondheimer theory with a mode-dependent $p$ to the calculated $\kappa$ for any surface orientation or thickness (Fig. S6)[13]. The (111) surface case has the largest roughness. Here, we note that the extracted $\eta$ is also anisotropic due to the anisotropic $\kappa$ for the (110) surface case. Spectral $\kappa$ results were calculated by explicitly accounting for the atomic structure of the thin film and by applying the Sondheimer theory with the obtained $\eta$, as shown in Figs. 2(b,c). Except for the thinnest films, the overall features of spectral $\kappa$ are similar. Therefore, the Sondheimer theory with an adjusted $p$ is seemingly able to reproduce the present calculations. However, among the frequency-dependent phonon mean free paths shown in Fig. S7, a large discrepancy can be seen, indicating that the adjustment of $p$ cannot explain the heat conduction mechanism in thin films. Thus, we conclude that tuning the surface specularity is not valid based on the following findings. (1) The considered thin films do not have surface roughness. (2) The anisotropic surface roughness for the (110) surface case and thickness-dependent $\eta$ are not acceptable. (3) The magnitude of the extracted $\eta$ is significantly larger than the root mean square displacement (Fig. S6)[15]. Thus, we speculate that surface phonons are strongly relevant to the mechanism of heat conduction in thin films.

To verify our hypothesis, we must decompose a surface phonon mode and a phonon mode that is localized within the thin film (referred to as an inner phonon).
Subsequently, we must quantitatively evaluate the influence of three-phonon scattering involving both surface and inner phonons on the \( \kappa \) values of a thin film. For decomposition, we apply the atomic participation ratio (APR)[16]. For a phonon mode \( q \) characterized by wavevector \( k \) and polarization \( j \), \( F_q^{\text{APR}}(b) \) indicates how the eigenvector of phonon mode \( q \) is localized at the \( b \)th atom in a unit cell, given by

\[
F_q^{\text{APR}}(b) = \frac{|e_q(b)|^2}{M_b} \left( \sum_{b'} \frac{|e_q(b')|^4}{M_{b'}} \right)^{-1/2},
\]

where \( N_b, e_q(b), \) and \( M_b \) denote the number of atoms in a unit cell, the eigenvector of the \( b \)th atom of phonon mode \( q \), and the mass of the \( b \)th atom, respectively. \( F_q^{\text{APR}}(b) \) is unity when phonon mode \( q \) is completely localized at the \( b \)th atom and is \( 1/\sqrt{N_b} \) for complete delocalization. Because there are two surfaces at the top and bottom of a thin film, we use \( F_q^{\text{APR}}(b) \) for the two outermost surface atoms in the decomposition. Here, the outermost surface is defined as the surface in contact with the vacuum layer.

Figure 3(a) shows a color map of \( F_q^{\text{APR}}(b) \) for the outermost surface atoms projected onto the dispersion relation of the \( \langle 100 \rangle \) thin film with \( t = 5.5 \) nm. The \( F_q^{\text{APR}}(b) \) results for the four phonon modes specified in Fig. 3(a) are shown in Figs. 3(b–e). For the acoustic mode [Fig. 3(b)], \( F_q^{\text{APR}}(b) \) is uniformly distributed and identical to \( 1/\sqrt{N_b} \). In contrast, for the phonon mode [Fig. 3(c)], \( F_q^{\text{APR}}(b) \) is large for the outermost surface atoms, indicating that this mode is completely localized at the surface. The hybridization of the surface and inner vibrations depends on the phonon mode. Therefore, the value of \( F_q^{\text{APR}}(b) \) for decomposing the surface phonons cannot be uniquely determined. Additionally, the surface atomic density and specific surface area
depend on the surface orientation and thickness, respectively. Thus, a single threshold value for $F_q^{\text{APR}}(b)$ may not be appropriate. Nevertheless, we employed a single threshold value $F_{\text{thr}}^{\text{APR}}$ and set it to 0.3, which is reasonable for the decomposition of surface phonons[13]. As shown in Fig. 3(a), the surface phonon modes illustrated in Fig. 1(c) are successfully identified by $F_{\text{thr}}^{\text{APR}} = 0.3$. Some optical modes below 5 THz correspond to hybridized surface and inner phonons. However, because the magnitude of $F_q^{\text{APR}}(b)$ is relatively large for the outermost surface atoms, those optical modes are classified as surface phonons. The impact of $F_{\text{thr}}^{\text{APR}}$ on the decomposition and $\kappa$ evaluation is discussed in the Supplemental Material[13].

Three-phonon scattering processes are classified into those (1) with only inner phonons, (2) with only surface phonons, and (3) involving surface and inner phonons. Among the three types, we neglected scatterings involving surface and inner phonons and then calculated the thickness-dependent $\kappa$ [Fig. 4(a)]. Here, we plot results for the case in which surface phonons are successfully decomposed. We also show results from the bulk-adopted method for comparison. Interestingly, the absence of surface–inner phonon scattering increases $\kappa$ for all surface orientations; thus, surface–inner phonon scattering dominates the overall heat conduction in thin films. While the $\kappa$ results for the $\langle 100 \rangle$ and $\langle 111 \rangle$ surface orientations approach that of bulk silicon, $\kappa$ for the $\langle 110 \rangle$ surface orientation largely exceeds the bulk value due to the high group velocities of surface phonons for this orientation. The number of surface phonon modes shows only a slight dependence on the thickness; however, because its value is approximately 20% of the overall vibrational modes, the contribution of surface phonons to heat conduction
cannot be neglected. The magnitude and thickness dependence of $\kappa$ for inner phonons ($\kappa_{\text{inner}}$) exhibit interesting trends. In the absence of surface–inner phonon scattering, the $\kappa_{\text{inner}}$ values for the different surface orientations are comparable, and the thickness dependence of $\kappa_{\text{inner}}$ is weak. Thus, we conclude that surface–inner phonon scattering characterizes the surface-orientation dependence of $\kappa$.

To further investigate the influence of surface–inner phonon scatterings, we calculated the frequency-dependent relaxation times of inner and surface phonons (Figs. S10–S12). Interestingly, the magnitude and frequency dependence of the relaxation times of inner phonons are close to those of bulk, indicating that inner–inner phonon scatterings are similar to those in bulk. In contrast, except for high-frequency surface phonons, the frequency dependence of the relaxation times for surface phonons is characterized by surface–surface phonon scatterings. As shown in Fig. 4(b), the frequency dependence of spectral $\kappa$ without surface–inner phonon scattering is close to that of bulk. In particular, the peak center of spectral $\kappa_{\text{inner}}$ is the same as that of bulk, and the overall features of the frequency-dependent $\kappa_{\text{inner}}$ are similar to those of bulk. Furthermore, the heat conduction contribution of surface phonons at approximately 3 THz, which corresponds to the $S_1$ mode, is suppressed by 50%. We found that this suppression is primarily caused by three-phonon scattering involving two $S_1$ surface phonons and one inner phonon in the vicinity of 6 THz (i.e., $S_1+S_1\rightarrow$inner phonon and vice versa).

In summary, we have applied ALD methods to study silicon ultra-thin films with thicknesses of 0.3–11 nm. We have investigated the applicability of the widely used
Sondheimer theory as well as the influence of surface phonons on heat conduction in these thin films. It has been proposed that the Sondheimer theory with a tuned surface specularity can explain the thickness-dependent thermal conductivity of ultra-thin films. However, unrealistic surface specularity values are required. In this sense, the Sondheimer theory cannot be applicable to ultra-thin films due to the presence of surface phonons. By decomposing surface and inner phonons with the APR, we carefully investigated the influence of surface–inner phonon scattering channels on the transport properties of thin films. The results show that surface–inner phonon scattering significantly affects the overall heat conduction in thin films and characterizes surface-orientation-dependent phonon transport properties.

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References

(Oxford University Press, 2000).
Figures

Fig. 1 (a) Simulation model for a silicon ultra-thin film. (b,c) Phonon dispersion relations for ultra-thin silicon films with (100) surface orientation at thicknesses of 0.55 and 5.5 nm, respectively. The labels in (c) denote surface phonon modes.
Fig. 2 (a) Thickness-dependent thermal conductivities ($\kappa$) for three surface orientations at $T = 300$ K. The solid lines present results obtained from the Sondheimer theory for several surface specularity values ($\rho$). The cross marks denote results from previous experiments[17-24]. (b,c) Spectral $\kappa$ for ultra-thin films with $\langle 100 \rangle$ surface orientation for 0.55 and 5.5 nm at $T = 300$ K, respectively. The dashed and dotted curves present results obtained via the Sondheimer theory with $\rho = 0.8$ and the surface roughness produced by fitting, respectively.
Fig. 3 (a) Phonon dispersion relation of the ⟨100⟩ surface orientation for 5.5 nm projected by the atomic participation ratio (APR). The blue and yellow colors denote inner and surface phonons, respectively. (b–e) $F_{q}^{\text{APR}}(b)$ of the $b$th atom as a function of coordinates in the thickness direction ($z$-direction). The chosen phonon modes are specified in (a). The blue dashed line indicates the APR value for complete delocalization. The red dashed line indicates the threshold value used for $F_{q}^{\text{APR}}(b)$. 
Fig. 4 (a) Thickness-dependent $\kappa$ with and without surface–inner phonon scattering. The solid lines present results obtained from the Sondheimer theory, and the filled squares indicate results from the bulk-adopted method. (b) Spectral $\kappa$ of (100)-surface-oriented ultra-thin films with a thickness of 5.5 nm with and without surface–inner phonon scattering. The solid black line indicates the spectral $\kappa$ of bulk silicon.

Tables

This paper does not include tables.